Silicon NPN Power Transistors BU526 BU526A

DESCRIPTION

- With TO-3 package
- Short switching times.
- High dielectric strength.

APPLICATIONS

- For use in power supply units of TV receives.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	900	V
V_{CEO}	Collector-emitter voltage	BU526	Open base	400	V
		BU526A		460	
V_{EBO}	Emitter-base voltage		Open collector	7	V
I_C	Collector current			8	A
I_{CM}	Collector current-peak			10	A
P_T	Total power dissipation		T_C=25℃	86	W
T_j	Junction temperature			175	℃
T_{stg}	Storage temperature			-65~175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	1.04	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	BU526	I_C=50mA; I_B=0;	400			V
		BU526A		460			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		I_E=10mA; I_C=0;	7			V
$V_{CEsat-1}$	Collector-emitter saturation voltage		I_C=5A;I_B=1 A			1.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltage		I_C=8A;I_B=3 A			5.0	V
V_{BEsat}	Base-emitter saturation voltage		I_C=5A;I_B=1 A			1.6	V
I_{CBO}	Collector cut-off current		V_{CB}=900V;I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current		V_{EB}=7V;I_C=0			0.1	mA
h_{FE}	DC current gain		I_C=1A ; V_{CE}=5V	15		45	

PACKAGE OUTLINE

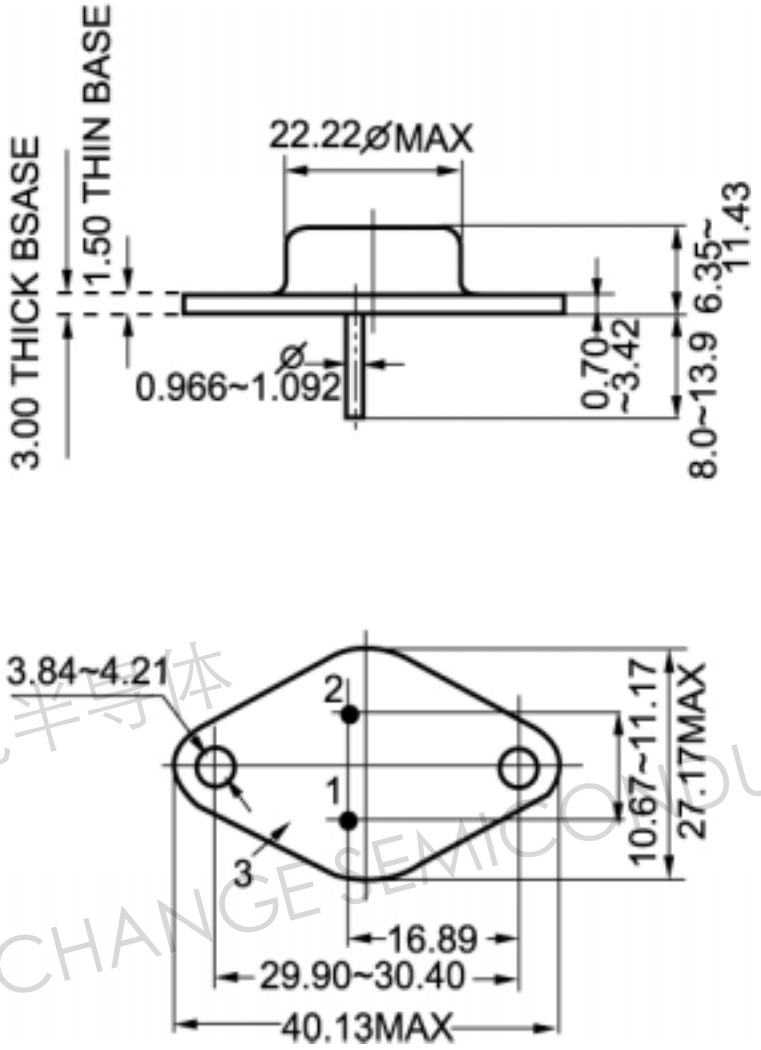

Fig.2 Outline dimensions